SiT1576 **Preliminary**

1.2mm² Micropower, Low-Jitter, 1Hz - 1MHz Programmable Super TCXO

SiTime™

The Smart Timing Choice™

Features

- 1 Hz to 1 MHz ±5 ppm all-inclusive frequency stability
- Factory programmable output frequency
- World's smallest TCXO Footprint: 1.2 mm²
  - 1.5 x 0.8 mm CSP
  - No external bypass cap required
- Improved stability reduces system power with fewer network timekeeping updates
- Ultra-low power: 8 µA (100 kHz)
- Supply voltage: 1.8V ±10%
- Operating temperature ranges: -20°C to +70°C, -40°C to +85°C
- Pb-free, RoHS and REACH compliant

Applications

- Health and wellness monitors
- Smart pens
- ULP input devices
- Proprietary wireless
- Sensor interface

INSTANT SAMPLES   GREEN SOLUTIONS   LIFETIME WARRANTY

TempFlat MEMS™

Electrical Characteristics

Conditions: Min/Max limits are over temperature, Vdd = 1.8V ±10%, unless otherwise stated. Typicals are at 25°C and Vdd = 1.8V.

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency and Stability						
Output Frequency	Fout	1		1M	Hz	
Total Frequency Stability [1]	F_stab	-5		5	ppm	All inclusive, Stability code: E
		-20		20	ppm	All inclusive, Stability code: 1
Allan Deviation	AD		1e-8	4e-8		1 second averaging time
First Year Frequency Aging	F_aging		±1		ppm	T_A = 25°C, Vdd = 1.8V
Jitter Performance						
Integrated Phase Jitter	IPJ		1.8	2.5	ns_{RMS}	F_{OUT} > 1 kHz. Integration bandwidth = 100 Hz to F_{OUT} /2. Inclusive of 50 mV peak-to-peak sinusoidal noise on Vdd. Noise frequency 100 Hz to 20 MHz.
Period Jitter	PJ		2.5	4	ns_{RMS}	Cycles = 10,000, f = 100kHz. Per JEDEC standard 65B
Peak-to-Peak Period Jitter	PJ$_{p-p}$		20	35	ns_{p-p}	
Supply Voltage and Current Consumption						
Operating Supply Voltage	Vdd	1.62	1.8	1.98	V	
Supply Current	Idd		2		µA	F_{OUT} = 1 Hz
			4.5			F_{OUT} = 33 kHz
			8			F_{OUT} = 100 kHz
			20			F_{OUT} = 1 MHz
Start-up Time at Power-up	t_start			300	ms	Measured when supply reaches 90% of final Vdd to the first output pulse.
Operating Temperature Range						
Operating Temperature Range	Op_Temp	-20		70	°C	"C" ordering code
		-40		85	°C	"I" ordering code
LVCMOS Output						
Output Rise/Fall Time	tr, tf		9	20	ns	10-90% (Vdd), 15 pF Load.
Output Clock Duty Cycle	DC	45		55	%	
Output Voltage High	VOH	90%			Vdd	I_{OH} = -1 µA
Output Voltage Low	VOL			10%	Vdd	I_{OL} = 1 µA

Note:

1. Relative to 32.768 kHz, includes initial tolerance, over temp stability, 3x reflow, Vdd range, board-level underfill, and 20% load variation. Tested with Agilent 53132A frequency counter. Measured with 100 ms gate time for accurate frequency measurement.

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Pin Configuration

CSP Pin	Symbol	I/O	Functionality
1	GND	Internal Test	Connect to ground.
2	CLK Out	OUT	Oscillator clock output.
3	Vdd	Power Supply	1.8V ±10% power supply. Under normal operating conditions, Vdd does not require external bypass/decoupling capacitor(s). SiT1576 includes on-chip filtering capacitors.
4	GND	Power Supply Ground	Connect to ground.

CSP Package (Top View)

GND (1) (4) GND

CLK Out (2) (3) Vdd
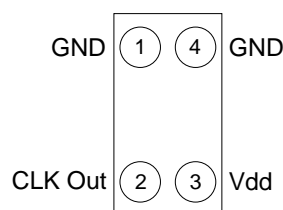
Absolute Maximum Ratings

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameters	Test Conditions	Value	Unit
Continuous Power Supply Voltage Range (Vdd)		-0.5 to 4.0	V
Continuous Maximum Operating Temperature Range		105	°C
Short Duration Maximum Operating Temperature Range	≤ 30 minutes	125	°C
Human Body Model (HBM) ESD Protection	JESD22-A114	2000	V
Charge-Device Model (CDM) ESD Protection	JESD22-C101	750	V
Machine Model (MM) ESD Protection	JESD22-A115	300	V
Latch-up Tolerance	JESD78 Compliant		
Mechanical Shock Resistance	Mil 883, Method 2002	20,000	*g*
Mechanical Vibration Resistance	Mil 883, Method 2007	70	*g*
1508 CSP Junction Temperature		150	°C
Storage Temperature		-65 to 150	°C

System Block Diagram
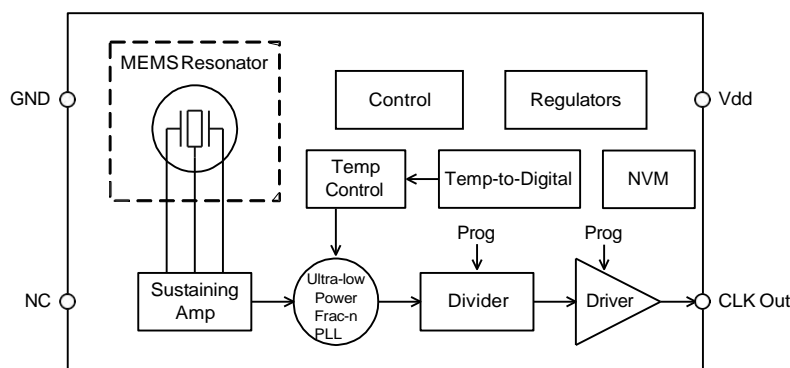
Figure 1. SiT1576 Block Diagram

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Description

SiT1576 is an ultra-small and ultra-low power Factory programmable TCXO with an output frequency range between 1 Hz to 1 MHz. SiTime's silicon MEMS technology enables the first 1 Hz - 1 MHz TCXO in the world's smallest footprint and chip-scale packaging (CSP). Typical supply current is 4.5 µA (33 kHz) under no load condition.

SiTime's MEMS oscillator consists of a MEMS resonator and a programmable analog circuit. SiT1576 MEMS resonator is built with SiTime's unique MEMS First™ process. A key manufacturing step is EpiSeal™ during which the MEMS resonator is annealed with temperatures over 1000°C. EpiSeal creates an extremely strong, clean, vacuum chamber that encapsulates the MEMS resonator and ensures the best performance and reliability. During EpiSeal, a poly silicon cap is grown on top of the resonator cavity, which eliminates the need for additional cap wafers or other exotic packaging. As a result, SiTime's MEMS resonator die can be used like any other semiconductor die. One unique result of SiTime's MEMS First and EpiSeal manufacturing processes is the capability to integrate SiTime's MEMS die with a SOC, ASIC, micropro- cessor or analog die within a package to eliminate external timing components and provide a highly integrated, smaller, cheaper solution to the customer.

TCXO Frequency Stability

SiT1576 is factory calibrated (trimmed) over multiple temperature points to guarantee extremely tight stability over temperature. Unlike quartz crystals that have a classic tuning fork parabola temperature curve with a 25°C turnover point with a 0.04 ppm/°C2 temperature coefficient, the SiT1576 temperature coefficient is calibrated and corrected over temperature with an active temperature correction circuit. The result is a 32 kHz TCXO with extremely tight frequency variation over the -40°C to +85°C temperature range.

When measuring the output frequency of SiT1576 with a frequency counter, it is important to make sure the counter's gate time is >100 ms. Shorter gate times may lead to inaccurate measurements.

Dynamic Temperature Frequency Response

Dynamic Temperature Frequency Response is the rate of frequency change during temperature ramps. This is an important performance metric when the oscillator is mounted near a high power component (e.g. SoC or power management) that may rapidly change the temperature of surrounding components.
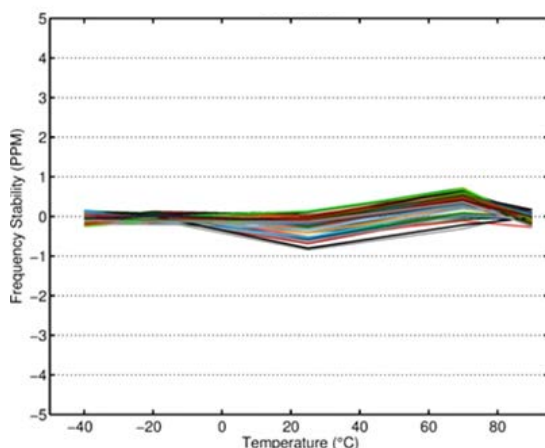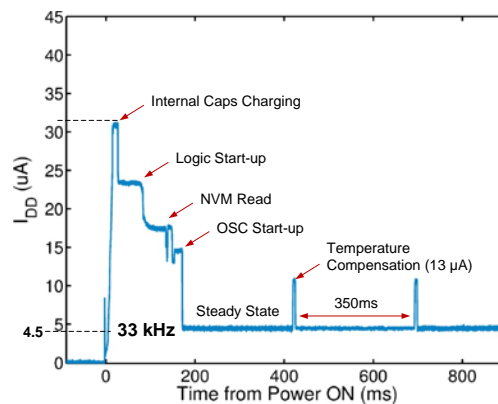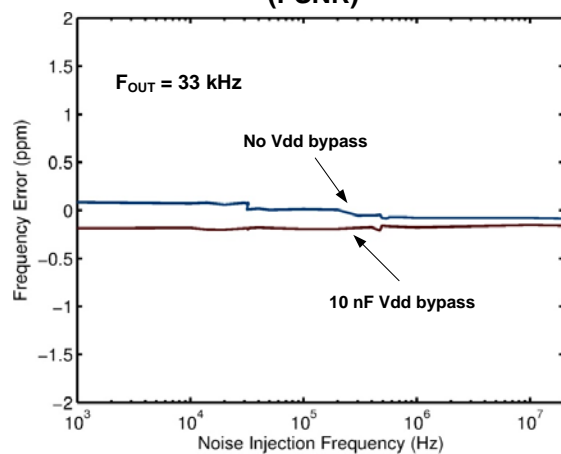
For moderate temperature ramp rates (< 2°C/sec), the dynamic response is primarily determined by the steady-state frequency vs. temperature of the device. The best dynamic response is obtained from parts which have been trimmed to be flat in frequency over temperature.

For high temperature ramp rates (>5°C/sec), the latency in the temperature compensation loop contributes a larger frequency error, which is dependent on the temperature compensation update rate. This part achieves excellent performance at 3Hz update rate. This device family supports faster update rates for further reducing dynamic frequency error at the expense of slightly increased current consumption.

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Typical Operating Curves
(T_A = 25°C, Vdd = 1.8V, unless otherwise stated)

Frequency Stability over Temperature (Post Reflow)

Start-up and Steady-State Current Profile

Power Supply Noise Rejection (PSNR)

Dynamic Frequency Response for Moderate Temperature Ramps
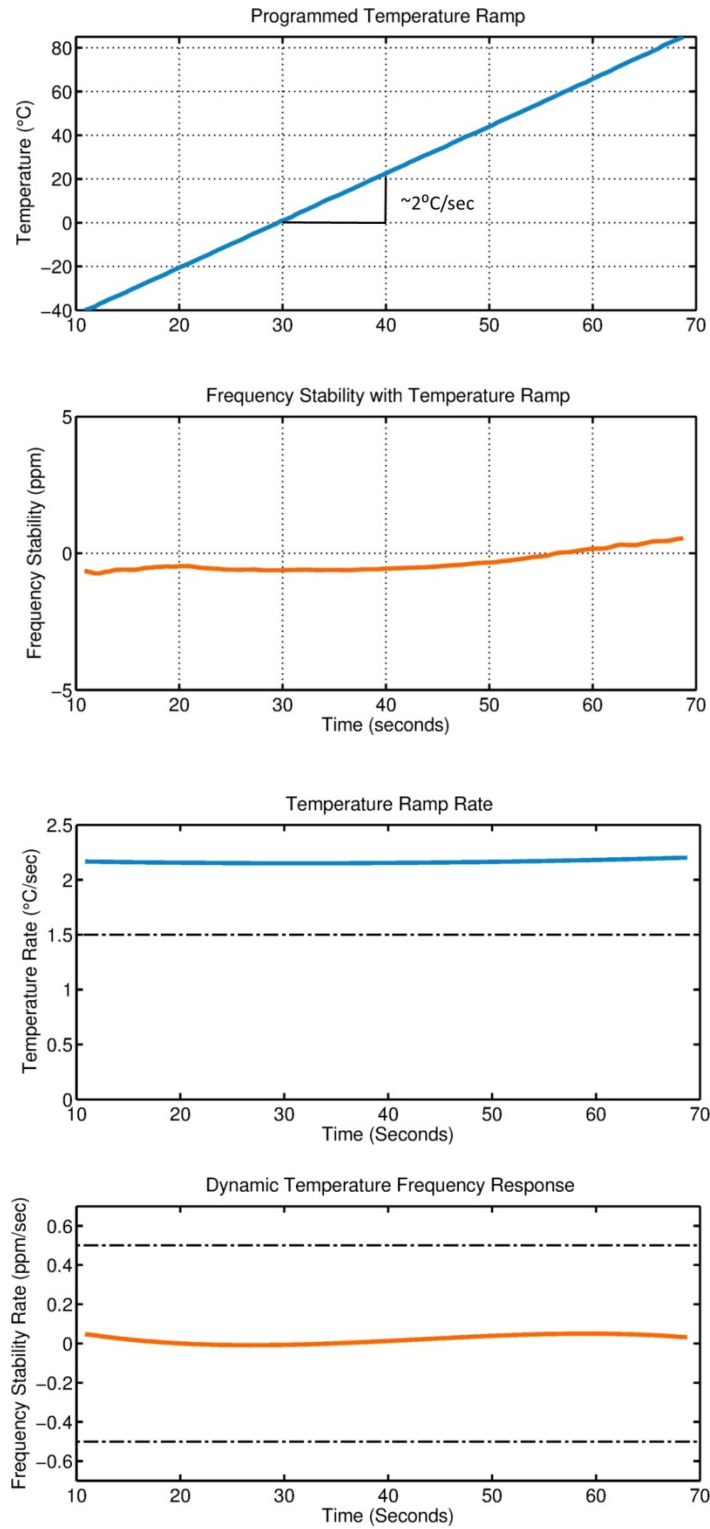
Frequency accuracy under a moderate temperature ramp up to 2°C/sec is limited by the TCXO's trimmed accuracy of the frequency stability over-temperature.

Note:

1. Measured relative to 32.768 kHz.

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Dynamic Frequency Response for Fast Temperature Ramps

5°C/sec Temp Ramp Frequency Response

10°C/sec Temp Ramp Frequency Response
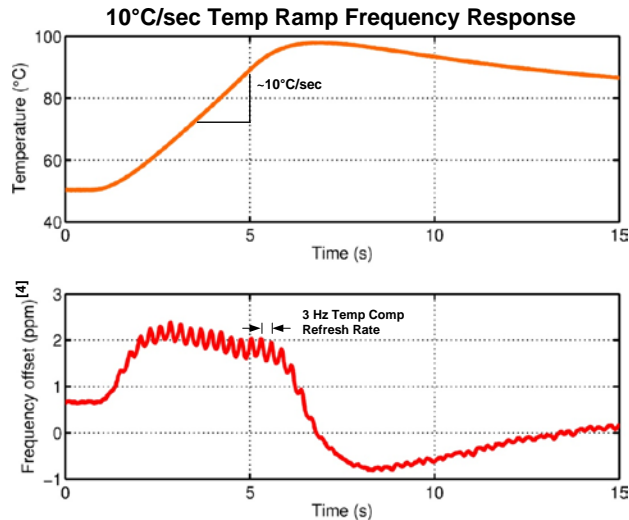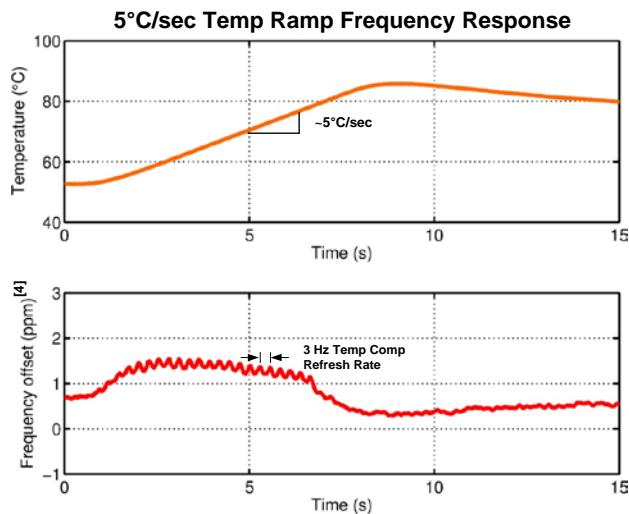
For temperature ramps >5°C/sec, the frequency accuracy is limited by the update rate of the temperature compensation path (see the 5°C/sec and 10°C/sec plots).

Contact Factory for applications that require improved dynamic performance.
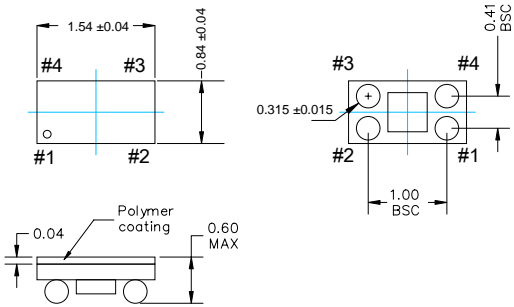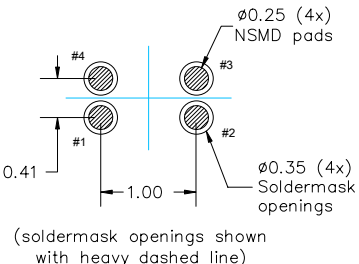
Note:
1. Referenced to 32.768 kHz.

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Dimensions and Patterns

Package Size – Dimensions (Unit: mm)	Recommended Land Pattern (Unit: mm)

1.55 x 0.85 mm CSP

1.54 ±0.04
0.84 ±0.04

#4   #3

#1   #2

0.41 BSC

#3   #4

0.315 ±0.015

#2   #1

1.00 BSC

Polymer coating

0.04   0.60 MAX

Ø0.25 (4x) NSMD pads

#4   #3

#1   #2

0.41

1.00

Ø0.35 (4x) Soldermask openings

(soldermask openings shown with heavy dashed line)

Recommended 4-mil (0.1mm) stencil thickness

Manufacturing Guidelines

1) No Ultrasonic or Megasonic cleaning: Do not subject SiT1576 to an ultrasonic or megasonic cleaning environment. Permanent damage or long term reliability issues may occur.

2) Applying board-level underfill and overmold is acceptable and will not impact the reliability of the device.

3) Reflow profile, per JESD22-A113D.

4) For additional manufacturing guidelines and marking/tape-reel instructions, click on the following link: http://www.sitime.com/component/docman/doc_download/243-manufacturing-notes-for-sitime-oscillators

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Ordering Information

SiT1576AI-JE-18E-XXXX.XXXXS

Part Family
"SiT1576"

Revision Letter
"A": is the revision

Temperature Range
"C": Extended Commercial, -20 to 70ºC
"I": Industrial, -40 to 85ºC

Package Size
"J": 1.5 mm x 0.8 mm CSP

All-Inclusive Over Temp Stability
"E": ±5 ppm
"1": ±20 ppm

Packaging
"S": 8 mm Tape & Reel, 10ku reel
"D": 8 mm Tape & Reel, 3ku reel
"E": 8 mm Tape & Reel, 1ku reel

Samples in cut Tape

Output Frequency
1000.0000 = 1.000 MHz
0100.0000 = 100.000 kHz
0010.0000 = 10.000 kHz
0001.0000 = 1.000 kHz
0000.1000 = 100 Hz
0000.0100 = 10 Hz
0000.0010 = 1 Hz

Supply Voltage: 1.8V ±10%

Revision History

Revision	Release Date	Change Summary
0.25	1/13/16	Initial Release of Advanced datasheet
0.5	3/10/16	Preliminary datasheet initial release